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L Number	Hits	Search Text	DB	Time stamp
-	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/18 17:55
-	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/18 17:55
-	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
_	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
-	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
_	249	lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
_	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
_	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18
_	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	8141	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58

	_9373	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or Infert\$1 o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:02
_	152308	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18
_	140917	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
	1922	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 17:36

			_	
-	15865	(amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/18 18:04
-	39181	(amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/15 18:05
_	30917	(amorphous or amorph\$9) near3 film\$1	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/03/15 18:11
			EPO; JPO; DERWENT; IBM_TDB	
-	67049	((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15
	204	near3 film\$1) (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (lateral\$4 near7 (MOS or MOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-MOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1)) or (latera		2002/03/15 18:12
_	5147	near3 film\$1)) implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:07

1 69 ((LDMO332 OL LD-MO342 OL (LD dd) 110545	002/03/15
or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj EPO; JPO; metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or	3:25
MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or (lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or	
metal adj oxide adj semiconduct\$4) or DERWENT; (lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or	
(lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or	
MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or	
(LDD adj MOS\$3) or LDDMOSFET\$1 or	
LDD add MOSFETS1 or (LDD add MOSFETS1)) or	
100 Modelly of Amble and difficulty	
((lateral\$4 adj double adj diffus\$5 adj	
metal adj oxide adj semiconduct\$4) or	,
(lateral\$4 adj double-diffus\$5 adj metal	·
adj oxide adj semiconduct\$4)) or	
(lateral\$4 adj double adj diffus\$5 adj	
(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7	
(metal adj oxide adj semiconduct\$4)) or	
(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS	
or NMOSFET\$1 or PMOS or PMOSFET\$1)) or	
(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)	
or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj	
PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or	
(LD adj NMOS\$3) or LDNMOSFET\$1 or	
LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or	
(lateral\$4 near7 (DMOS or DMOSFET\$1)) or	
(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS	
or NMOSFET\$1 or PMOS or PMOSFET\$1 or	
FET\$1 or transistor\$1 or IGFET\$1 or	
(insulat\$5 adj gate adj field adj effect	
adj transistor\$1)))) and ((gate\$1 or	
electrode\$1) and source\$1 and drain\$1)	
and ((field adj (oxide\$1 or isolat\$5)) or	
LOCOS\$2 or trench\$2 or STI\$1 or (shallow	
adj trench\$2 adj isolat\$5))) and	
(((amorphous or amorph\$9) near3 (region\$1	
or area\$1 or part\$1 or portion\$1 or	
element\$1)) or ((amorphous or amorph\$9)	
near3 (layer\$1 or substrate\$1 or	
wafer\$1)) or ((amorphous or amorph\$9)	
near3 film\$1))) and (implant\$8 adj	
(silicon or Si or "Si" or Ge or "Ge" or	
germanium))	000 /00 /15
430 (((amorphous of amorphits) mours (- 3	002/03/15
Of aleast of parcet of portioner of	.8:47
element\$1)) or ((amorphous or amorph\$9) EPO; JPO;	
near3 (layer\$1 or substrate\$1 or DERWENT;	
wafer\$1)) or ((amorphous or amorph\$9) IBM_TDB	
near3 film\$1)) same (implant\$8 adj	
(silicon or Si or "Si" or Ge or "Ge" or	
germanium))	

	002/03/15 8:26
or LDMOSFET\$1 or LD-MOSFET\$1 of (LD add) MOSFET\$1) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB)	0.20
MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj EPO; GPO; metal adj oxide adj semiconduct\$4) or DERWENT; (lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB	
metal adj oxide adj semiconduct\$4) or DERWENT; (lateral\$4 adj diffus\$5 adj (MOS\$3 or IBM_TDB	
MOSFETS1)) or (LDDMOS\$2 or LDD-MOS\$2 or	
PRODUCTOR (ADDITION)	
/IDD adi MOSS3) or LDDMOSFET\$1 or	į.
IDD-MOSFETS1 or (LDD adi MOSFETS1)) or	Į
//lateral\$4 adj double adj diffus\$5 ad]	
metal adi oxide adi semiconduct\$4) or	ì
(lateral\$4 adj double-diffus\$5 adj metal	
adi oxide adi semiconduct\$4)) or	
(lateral\$4 adj double adj diffus\$5 ad)	İ
(MOS\$3 or MOSFET\$1)) or (lateral\$4 near/	
(metal adj oxide adj semiconduct\$4)) or	
(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS	ļ
or NMOSFETS1 or PMOS or PMOSFETS1)) or	
/I.DPMOS\$2 or I.D-PMOS\$2 or (LD adj PMOS\$3)	ļ
or LDPMOSFETS1 or LD-PMOSFET\$1 or (LD ad)	
(ID add NMOS\$3) or LDNMOSFET\$1 or	
LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or	
(lateral\$4 near7 (DMOS or DMOSFET\$1)) or	
(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS	
or NMOSFET\$1 or PMOS or PMOSFET\$1 or	
FET\$1 or transistor\$1 or IGFET\$1 or	
(insulat\$5 adj gate adj field adj effect	
adi transistor\$1)))) and (((amorphous of	
amorph\$9) near3 (region\$1 or area\$1 or	
part\$1 or portion\$1 or element\$1)) or	
((amorphous or amorph\$9) near3 (layer\$1	
or substrate\$1 or wafer\$1)) or	
((amorphous or amorph\$9) near3 film\$1))	
same (implant\$8 adj (silicon or Si or	
"Si" or Ge or "Ge" or germanium))) "Si" or Ge or "Ge" or germanium))) "Si" or Ge or "Ge" or germanium)))	2002/03/15
1 330 (((amorphous of allorphis)) fleats (togional formation)	18:47
or areasi or partsi or politionsi or	20.11
I heart (lavers) of substractor of	
near3 film\$1)) with (implant\$8 adj	
(silicon or Si or "Si" or Ge or "Ge" or	
germanium))	

	22	((((amorphous or amorph\$9) near3	USPAT;	2002/03/15
	""	(region\$1 or area\$1 or part\$1 or	US-PGPUB;	18:50
		portion\$1 or element\$1)) or ((amorphous	EPO; JPO;	
		or amorph\$9) near3 (layer\$1 or	DERWENT;	
	1	substrate\$1 or wafer\$1)) or ((amorphous	IBM TDB	
		1 · · · · · · · · · · · · · · · · · · ·	1511_155	
		or amorph\$9) near3 film\$1)) with		
		(implant\$8 adj (silicon or Si or "Si" or		
		Ge or "Ge" or germanium))) and ((LDMOS\$2		
		or LD-MOS\$2 or (LD adj MOS\$3) or		
		LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	!	
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or]	
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
	1	((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
•		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
	İ	(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
1 .		adj transistor\$1))))		
-	23681	(((amorphous or amorph\$9) near3 (region\$1	USPAT;	2002/03/15
		or area\$1 or part\$1 or portion\$1 or	US-PGPUB;	18:51
		element\$1)) or ((amorphous or amorph\$9)	EPO; JPO;	
		near3 (layer\$1 or substrate\$1 or	DERWENT;	
		wafer\$1)) or ((amorphous or amorph\$9)	IBM_TDB	1
		near3 film\$1)) with (substrate or wafer)		
-	244	(implant\$8 adj (silicon or Si or "Si" or	USPAT;	2002/03/15
	1	Ge or "Ge" or germanium)) same	US-PGPUB;	18:51
		((((amorphous or amorph\$9) near3	EPO; JPO;	
		(region\$1 or area\$1 or part\$1 or	DERWENT;	
		portion\$1 or element\$1)) or ((amorphous	IBM TDB	
		or amorph\$9) near3 (layer\$1 or	-	
		substrate\$1 or wafer\$1)) or ((amorphous		
		or amorph\$9) near3 film\$1)) with		
		(substrate or wafer))		
l .	1	(Danserace of Marct)	1	1

<u> </u>	16	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)	USPAT;	2002/03/15
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	US-PGPUB;	18:52
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj	EPO; JPO;	i
		metal adj oxide adj semiconduct\$4) or	DERWENT;	
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	IBM_TDB	
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		· ·
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
	1	(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
ŀ		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		<pre>(insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((implant\$8 adj</pre>		
1		adj transistorsi)))) and ((implantso adj		
		(silicon or Si or "Si" or Ge or "Ge" or		
		germanium)) same ((((amorphous or amorph\$9) near3 (region\$1 or area\$1 or		
		part\$1 or portion\$1 or element\$1)) or		
		((amorphous or amorph\$9) near3 (layer\$1		
		or substrate\$1 or wafer\$1)) or		
		((amorphous or amorph\$9) near3 film\$1))		Į l
		((amorphous of amorphiss) hears films;) with (substrate or wafer)))		
	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or	USPAT;	2002/03/18
-	720	LDMOS\$2 of LD-MOS\$2 of (LD adj Mos\$3) of LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	US-PGPUB;	17:55
			EPO; JPO;	
		MOSFET\$1)	DERWENT;	
	!		IBM TDB	
	51	lateral\$4 adj diffus\$5 adj metal adj	USPĀT;	2002/03/18
-	31	oxide adj semiconduct\$4	US-PGPUB;	17:55
		Oxide day semiconducty.	EPO; JPO;	
			DERWENT;	i
			IBM TDB	
_	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or	USPAT;	2002/03/18
		MOSFET\$1)	US-PGPUB;	17:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)	USPAT;	2002/03/18
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD	US-PGPUB;	17:56
		adj MOSFET\$1)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	74		USPAT;	2002/03/18
		metal adj oxide adj semiconduct\$4) or	US-PGPUB;	17:56
		(lateral\$4 adj double-diffus\$5 adj metal	EPO; JPO;	
		adj oxide adj semiconduct\$4)	DERWENT;	
1			IBM_TDB	0000/00/100
-	178		USPAT;	2002/03/18
		(MOS\$3 or MOSFET\$1)	US-PGPUB;	17:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/02/10
-	250		USPAT;	2002/03/18
1		semiconduct\$4)	US-PGPUB;	17:57
			EPO; JPO;	
			DERWENT;	
1	į.	I and the second	IBM TDB	i

-	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
_	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58
_	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59
	9374	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LD adj NMOSFET\$1 or LD-NMOSFET\$1 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:03	
_	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44

		_		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (mos adj semiconduct\$4)) or (lateral\$4 adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOS\$2) or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or Insulat\$5 adj gate adj field adj effect adj transistor\$1))) and ((amorphous or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:06
_	· 5148	amorph\$9) same (substrate or wafer)) implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13
_	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09
-	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22
_	7645	<pre>implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24
	26134	<pre>(implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25

-	176	((implant\$8 adj (silicon or Si or "Si" or	USPAT;	2002/03/18
		Ge or "Ge" or germanium)) or (implant\$8	US-PGPUB;	18:25
		near8 (silicon or Si or "Si" or Ge or	EPO; JPO;	
		"Ge" or germanium)) or (implant\$8 with	DERWENT;	
		((silicon or Si or "Si" or Ge or "Ge" or	IBM_TDB	
		<pre>germanium) near2 (ion\$1 or atom\$1)))) and</pre>		
		(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
}		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
	i	((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
Į.		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		İ
1	ļ	or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
1		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1)))) and ((amorphous or		
		amorph\$9) same (substrate or wafer)))	1	
-	152356	(gate\$1 or electrode\$1) and source\$1 and	USPAT;	2002/03/18
		drain\$1	US-PGPUB;	18:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	141012	(field adj (oxide\$1 or isolat\$5)) or	USPAT;	2002/03/18
		LOCOS\$2 or trench\$2 or STI\$1 or (shallow	US-PGPUB;	18:37
		adj trench\$2 adj isolat\$5)	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	

				T 2002 /02 /19
-	120	(((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	18:38
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1		
	١	or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2		
		or (LD adj MOS\$3) or LDMOSFET\$1 or		
		LD-MOSFET\$1 or (LD adj MOSFET\$1)) or		
	Ì	(lateral\$4 adj diffus\$5 adj metal adj		
		oxide adj semiconduct\$4) or (lateral\$4		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		1
		(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)	1	
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD		
		adj MOSFET\$1)) or ((lateral\$4 adj double		
		adj diffus\$5 adj metal adj oxide adj		
		semiconduct\$4) or (lateral\$4 adj		
		double-diffus\$5 adj metal adj oxide adj		1
		semiconduct\$4)) or (lateral\$4 adj double	1	
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
		(lateral\$4 near7 (metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 near7 (MOS		
		or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS		
		or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2		
		or (LD adj PMOS\$3) or LDPMOSFET\$1 or		İ
		LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or		
		(LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3)		
		or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj]
		NMOSFET\$1)) or (lateral\$4 near7 (DMOS or		1
		DMOSFET\$1)) or (lateral\$4 adj8 (MOS or		
		MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or		
		PMOSFET\$1 or FET\$1 or transistor\$1 or		
		IGFET\$1 or (insulat\$5 adj gate adj field		
		adj effect adj transistor(1)))) and		
		((amorphous or amorph\$9) same (substrate		
		or wafer)))) and ((field adj (oxide\$1 or		
		isolat\$5)) or LOCOS\$2 or trench\$2 or		
		STI\$1 or (shallow adj trench\$2 adj		
		isolat\$5))		

	1255	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:44
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
_	280	or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOSFET\$1)) or (LD adj NMOSFET\$1)) or (LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))) (((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj MOSFET\$1)) or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	18:45
		(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS		
		or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (amorphous or amorph\$9)		

 ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)) and (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOS\$3) or LDDMOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOS\$5) or LDPMOSFET\$1 or (LD adj PMOS\$2 or LD-NMOS\$2 or LD-NMOS\$2 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1 or NMOS or NMOSFET\$1 or LD-PMOSFET\$1 or LD-NMOSFET\$1 or NMOS or NMOSFET\$1 or LD-NMOSFET\$1 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:46

2002/03/18 (((implant\$8 adj (silicon or Si or "Si" USPAT; US-PGPUB; 19:54 or Ge or "Ge" or germanium)) or EPO; JPO; (implant\$8 near8 (silicon or Si or "Si" DERWENT; or Ge or "Ge" or germanium)) or IBM_TDB (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) or ((((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))) and (amorphous or amorph\$9))

Search History 10/20

10/20/02 11:25:11 AM

		•		
	848	<pre>((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
-	45	with (amorphous or amorph\$9) with (substrate or wafer) (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si"	USPAT; US-PGPUB; EPO; JPO;	2002/03/18
		or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or	DERWENT; IBM_TDB	
		<pre>amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or</pre>		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or		
_	1853	<pre>(insulat\$5 adj gate adj field adj effect adj transistor\$1)))) ((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8</pre>	USPAT; US-PGPUB;	2002/03/18 19:58
		near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))))	EPO; JPO; DERWENT; IBM_TDB	

-	78	(((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	19:58
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	1
		or Ge or "Ge" or germanium) near2 (ion\$1	_	
		or atom\$1)))) same (amorphous or		
İ		amorph\$9) same (substrate or wafer)) and		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		İ
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or	ĺ	
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		1
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		<pre>(metal adj oxide adj semiconduct\$4)) or</pre>		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS	1	
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
[(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)	1	
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or	1	
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
]	(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1))))		
-	43237	(crystall\$9 or re-crystall\$9 or (re adj	USPAT;	2002/03/18
		crystall\$9)) with amorph\$9	US-PGPUB;	21:53
		• • • • • • • • • • • • • • • • • • •	EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	8629	gaussian with (distribut\$6 or profil\$4)	USPAT;	2002/03/18
			US-PGPUB;	21:55
		•	EPO; JPO;	
			DERWENT;	
]			IBM TDB	

2002/03/18 21:56
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<u>-</u>	3	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	21:56
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1	_	
1		or atom\$1)))) same (amorphous or		
		amorph\$9) same (substrate or wafer)) and		
ĺ		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or	,	
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
İ		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		:
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		ļ
l		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		İ
		(metal adj oxide adj semiconduct\$4)) or		
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)	j	
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj	1	
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
	Ì	FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect	i	
		adj transistor\$1))))) and ((crystall\$9 or	1	
		re-crystall\$9 or (re adj crystall\$9))		
	1	with amorph\$9) and (gaussian with		1
		(distribut\$6 or profil\$4))		
L		(discribacs of brottisal)		<u> </u>

	6	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
-			US-PGPUB;	21:58
	1	or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si"		21.50
			EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1		
	1	or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2		1
	1	or (LD adj MOS\$3) or LDMOSFET\$1 or		
·		LD-MOSFET\$1 or (LD adj MOSFET\$1)) or		
		(lateral\$4 adj diffus\$5 adj metal adj		
		oxide adj semiconduct\$4) or (lateral\$4		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
	1	(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3)		İ
		or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD		1
		adj MOSFET\$1)) or ((lateral\$4 adj double		
ļ i		adj diffus\$5 adj metal adj oxide adj		
1		semiconduct\$4) or (lateral\$4 adj		
		double-diffus\$5 adj metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 adj double		
		adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or		
	i i	(lateral\$4 near7 (metal adj oxide adj		
		semiconduct\$4)) or (lateral\$4 near7 (MOS		
		or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS		
		or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2		j
	ļ	or (LD adj PMOS\$3) or LDPMOSFET\$1 or		
	ļ	LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or		
	1	(LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3)		
		or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj		
		NMOSFET\$1)) or (lateral\$4 near7 (DMOS or		
	ļ	DMOSFET\$1)) or (lateral\$4 adj8 (MOS or		
		MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or		
		PMOSFET\$1 or FET\$1 or transistor\$1 or		
		IGFET\$1 or (insulat\$5 adj gate adj field		
1		adj effect adj transistor\$1)))) and		
		((amorphous or amorph\$9) same (substrate		
	1	or wafer)))) or ((((implant\$8 adj		
		(silicon or Si or "Si" or Ge or "Ge" or	:	
	-	germanium)) or (implant\$8 near8 (silicon		
		or Si or "Si" or Ge or "Ge" or		
	ĺ	germanium)) or (implant\$8 with ((silicon		
	1	or Si or "Si" or Ge or "Ge" or germanium)		
		near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2	•	
1		or LD-MOS\$2 or (LD adj MOS\$3) or		
ļ.		LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj	1	
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		1
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or	1	
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
	j	PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or	1	
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1))))) and (amorphous or		
		<pre>amorph\$9))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9))</pre>		
Search Histo	ory 1	0With0amolph\$911aHH (gaBBgfah0with		
	-	(distribut\$6 or profil\$4))		
		2008\09755828 wen	<u> </u>	

_	25	((((implant\$8 adj (silicon or Si or "Si"	USPAT;	2002/03/18
		or Ge or "Ge" or germanium)) or	US-PGPUB;	21:59
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
		or Ge or "Ge" or germanium)) or	DERWENT;	
		(implant\$8 with ((silicon or Si or "Si"	IBM TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1	-	
]	or atom\$1)))) with (amorphous or		
1		amorph\$9) with (substrate or wafer)) and		
		((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
	1	MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
1		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		İ
		((lateral\$4 adj double adj diffus\$5 adj		1
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or	İ	
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or		ł
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj		
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		İ
ļ		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS	1	
		or NMOSFET\$1 or PMOS or PMOSFET\$1 or		
		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1))))) and ((crystall\$9 or		
		re-crystall\$9 or (re adj crystall\$9))		
		with amorph\$9)		
L	.1			

	35	////implanted and /giligen on Si on "Si"	USPAT;	2002/03/18
-	35	((((implant\$8 adj (silicon or Si or "Si"		
		or Ge or "Ge" or germanium)) or	US-PGPUB;	21:59
		(implant\$8 near8 (silicon or Si or "Si"	EPO; JPO;	
!		or Ge or "Ge" or germanium)) or	DERWENT;	
1		(implant\$8 with ((silicon or Si or "Si"	IBM_TDB	
		or Ge or "Ge" or germanium) near2 (ion\$1		
ļ		or atom\$1)))) same (amorphous or		
·		amorph\$9) same (substrate or wafer)) and		
,	ļ	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3)		
-		or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj		
		MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj diffus\$5 adj (MOS\$3 or		
		MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or		
		(LDD adj MOS\$3) or LDDMOSFET\$1 or		
		LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or		
		((lateral\$4 adj double adj diffus\$5 adj		
		metal adj oxide adj semiconduct\$4) or		
		(lateral\$4 adj double-diffus\$5 adj metal		
		adj oxide adj semiconduct\$4)) or		
		(lateral\$4 adj double adj diffus\$5 adj		
		(MOS\$3 or MOSFET\$1)) or (lateral\$4 near7		
		(metal adj oxide adj semiconduct\$4)) or		ļ
		(lateral\$4 near7 (MOS or MOSFET\$1 or NMOS		
		or NMOSFET\$1 or PMOS or PMOSFET\$1)) or	İ	
		(LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3)		
		or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj	1	
		PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or		
		(LD adj NMOS\$3) or LDNMOSFET\$1 or		
		LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or		
		(lateral\$4 near7 (DMOS or DMOSFET\$1)) or		
		1 '		
		(lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS		
}		or NMOSFET\$1 or PMOS or PMOSFET\$1 or	1	
İ		FET\$1 or transistor\$1 or IGFET\$1 or		
		(insulat\$5 adj gate adj field adj effect		
		adj transistor\$1))))) and ((crystall\$9 or		
		re-crystall\$9 or (re adj crystall\$9))		
		with amorph\$9)		
-	1	("5874768").PN.	USPAT;	2002/03/19
			US-PGPUB	16:21

	4	ω	Ν	Н	
BRS	BRS	BRS	BRS	BRS	Type
L7	L4	L3	L2	Ľ1	L #
104	277	79	93	876	Hits
lateral\$4 adj diffus\$5 adj3 metal adj oxide adj semiconduct\$4	(lateral\$4 adj double adj diffus\$5 adj ((metal adj oxide adj semiconduct\$4) or MOS\$2 or MOSFET\$1 or NMOS\$2 or NMOSFET\$1) or (lateral\$4 adj double-diffus\$5 adj ((metal adj oxide adj semiconduct\$4) or MOSFET\$1 or MOS\$2 or MOSFET\$1 or MOS\$2 or PMOSFET\$1 or NMOS\$2 or PMOSFET\$1 or NMOS\$2 or NMOSFET\$1)	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1 or NMOS or PMOS or NMOSFET\$1 or PMOSFET\$1)	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or MOSFET\$1)	Search Text
USPAT; 3 US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	UB; PO; B	DBs
2002/10/20	2002/10/20	2002/10/20 13:22	2002/10/20 13:32	2002/10/20 13:20	Time Stamp
					Comme
					Error Defini tion
0	0	0	0	0	Err

Type	6 BRS	7 BRS	8 BRS	9 BRS	10 BRS	11 BRS	12 BRS
H #	Ľ 5	L6	L8	Г9	L10	L111	L12
Hits	V	U	982	160596	16999	41155	10445
Search Text	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LD-PMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	LDNMOS\$2 or LD-NMOS\$2 or US-PGPUB; (LD adj NMOS\$3) or LD-NMOSFET\$1 EPO; JPO; LDNMOSFET\$1 or LD-NMOSFET\$1 DERWENT; or (LD adj NMOSFET\$1)	1 or 2 or 3 or 4 or 5 or 6 or 7.	(gate\$1 or electrode\$1) and source\$1 and drain\$1	(amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	(amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)	(amorphous or amorph\$9) near3 surfac\$3
DBS	UB; PO; T;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	UB; PO; T;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	, O, B	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT;
Time Stamp	2002/10/20 13:33	2002/10/20 13:35	2002/10/20 13:35	2002/10/20 13:38	2002/10/20 13:41	2002/10/20 13:41	2002/10/20
nts							
tion							
ors	0	0	0	0	0	0	0

O			2002/10/20 14:35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	8 and 15	114	L19	BRS	19
0			2002/10/20 14:35	ЛВ; РО; В	8 and 17	VO	L18	BRS	18
0			2002/10/20 14:26	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	15 same 16	2443	L17	BRS	17
0			2002/10/20 14:26	B;	10 or 11 or 12	54828	L16	BRS	16
0			2002/10/20 14:44	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)	32605	L15	BRS	15
0			2002/10/20 13:44	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	8 and 9 and (10 or 11 or 12) and 13	9	L14	BRS	14
0			2002/10/20 14:25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	5506	L13	BRS	13
r Err ni ors	Error Defini tion	Comme	Time Stamp	DBs	Search Text	Hits	L #	Туре	

	Type	F #	Hits	arch Text	DBs USPAT;	Time Stamp	;amp
20	BRS	L20	2855	(implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)) with (amorphous or amorph\$9)	CON USPAT; "Ge" US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	PUB; JPO; JPO; DB); 3PUB; 2002/10/20 JPO; 14:44 INT;
21	BRS	L21	3000	implant\$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium) with (amorphous or amorph\$9)	USPAT; US-PGPU EPO; JP DERWENT IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	T; GPUB; 2002/10/20 JPO; 14:50 ENT;
22	2 BRS	L22	ω	8 and 21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	T; GPUB; 2002/10/20 JPO; 14:46 ENT; 14:46
23	3 BRS	L23	3809	(implant\$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium)) same (amorphous or amorph\$9)	USPAT; US-PGPU EPO; JP DERWENT IBM_TDB	or USPAT; or US-PGPUB; or EPO; JPO; DERWENT; IBM_TDB	T; GPUB; 2002/10/20 JPO; 14:51 ENT;
24	1 BRS	L24	10	8 and 23	USPAT; US-PGPU EPO; JP DERWENT	USPAT; US-PGPUB; EPO; JPO; DERWENT; DERMENT	YT; GPUB; 2002/10/20 JPO; 14:51 WENT;

N	
СП	
BRS	Type
	, i
L25	۲ #
9546	
	Hits
(LDMOS\$2 or LD-MOS\$2 or LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1) or (LDDMOS\$2 or LDD-MOS\$2 or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1) or ((lateral\$4 adj double adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj semiconduct\$4) or (lateral\$4 adj double adj semiconduct\$4)) or (lateral\$4 adj double adj semiconduct\$4)) or (lateral\$4 adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or pMOSFET\$1 or NMOS or LD-PMOS\$2 or (LD adj pMOS\$3) or LDPMOS\$2 or LD-PMOS\$5 or (LD adj pMOSFET\$1)) or (LD adj pMOSFET\$1)) or (LD adj pMOSFET\$1)) or (LD adj	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
200:	Time
2002/10/20	
/20	Stamp
	Comme nts
	Error Defini tion
0	Err

		
27	26	
BRS	BRS	Type
L27	H 22 6	# 1
9546	954 6	Hits
25 or 26	adj MOS\$3 or LD-MOS\$2 or (LD-MOSFET\$1 or (LD adj MOSFET\$1) or (Lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (LDDMOS\$2 or LDD-MOS\$2 or (LDDMOS\$2 or LDD-MOS\$2 or (LDDMOS\$5 adj MOS\$3) or (LDD adj MOS\$3) or (LDD adj MOSFET\$1) or (LDD adj MOSFET\$1)) or (Lateral\$4 adj double adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj oxide adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or (Lateral\$4 adj double adj semiconduct\$4)) or (lateral\$4 adj double adj semiconduct\$4) or (lateral\$4 adj oxide adj mear7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS\$2 or LD-PMOS\$2 or (LD adj pMOS\$2) or LD-PMOS\$2 or (LD adj pMOS\$2) or (LD adj pMO	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	DBs
2002/10/20 14:59	2002/10/20	Time Stamp
		Comme
		Error Defini tion
0	0	Err

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comme nts	Error Err Definiors	Err
					USPAT;		•••••		
		••••••			US-PGPUB;	0000/10/00			
28	BRS	L28	9546	8 or 27	EPO; JPO;	1/1.50			0
					DERWENT;	+ • (••••••	
		•••••			IBM_TDB				
					USPAT;				
		•••••	••••••		US-PGPUB;	2002/10/20			
29	BRS	L29	123	21 and 28	EPO; JPO;	15.01	•••••		0
					DERWENT;	F (••••••		
		•			IBM_TDB				
					USPAT;				
		*******			US-PGPUB;	3003/10/30	•••••		
30	BRS	L30	149	23 and 28	EPO; JPO;	15.01			0
		•••••			DERWENT;	F(. C)			
•		••••••			IBM TDB	••••		•••••	<u></u>
		•••			1	••	•••	•••	•